

**Silicon PNP Power Transistors**

**2SA887**

**DESCRIPTION**

- With TO-202 package
- Complement to type 2SC1848

**APPLICATIONS**

- Medium power amplifier

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

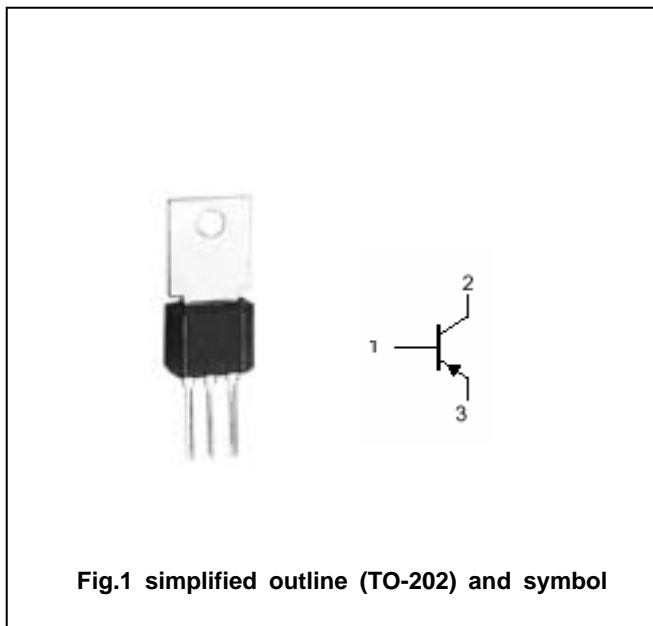


Fig.1 simplified outline (TO-202) and symbol

**Absolute maximum ratings (Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-70	V
$V_{CEO}$	Collector-emitter voltage	Open base	-50	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-2	A
$I_{CM}$	Collector current-peak		-3	A
$P_C$	Collector power dissipation	$T_a=25$	1.2	W
		$T_C=25$	10	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-50			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA; I <sub>E</sub> =0	-70			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1A ; I <sub>B</sub> =-0.1A		-0.6	-1.2	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A ; I <sub>B</sub> =-0.2 A		-1.0	-1.5	V
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-100mA ; V <sub>CE</sub> =-5V	30			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	50		220	
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-40V; I <sub>E</sub> =0			-1.0	μ A
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-20V; I <sub>B</sub> =0			-100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-10	μ A
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =0.5A ; V <sub>CB</sub> =-5V		150		MHz

◆ h<sub>FE-2</sub> Classifications

P	Q	R
50-100	80-160	120-220

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PACKAGE OUTLINE

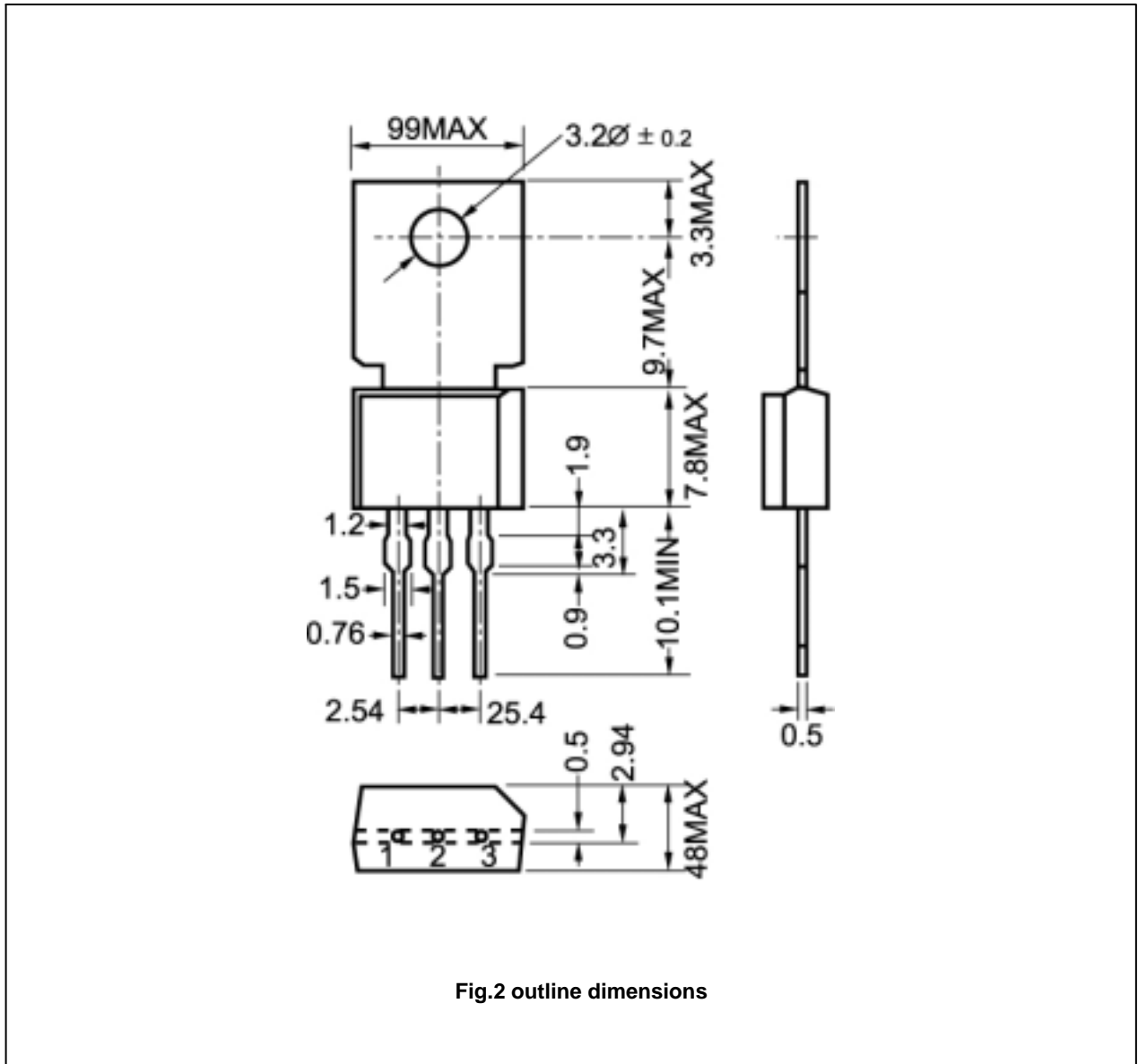


Fig.2 outline dimensions